



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-92L Plastic-Encapsulate Transistors

TPT5610 TRANSISTOR (PNP)

FEATURES

Power dissipation

P_{CM} : 1 W ($T_{amb}=25^{\circ}C$)

Collector current

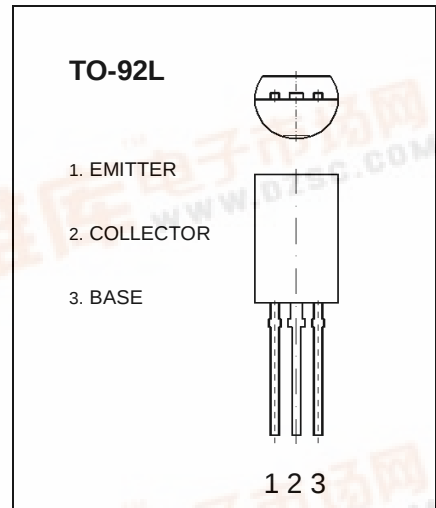
I_{CM} : -1 A

Collector-base voltage

$V_{(BR)CBO}$: -25 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-10\mu A, I_E=0$	-25			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1mA, I_B=0$	-20			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-10\mu A, I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-20V, I_E=0$			-1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-5V, I_C=0$			-1	μA
DC current gain	h_{FE}	$V_{CE}=-2V, I_C=-500mA$	60		240	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-800mA, I_B=-80mA$			-0.5	V
Base-emitter voltage	V_{BE}	$V_{CE}=-2V, I_C=-500mA$			-1	V
Transition frequency	f_T	$V_{CE}=-2V, I_C=-500mA$		350		MHz
Collector output capacitance	C_{ob}	$V_{CB}=-10V, I_E=0, f=1MHz$		38		pF

CLASSIFICATION OF h_{FE}

Rank	A	B	C
Range	60-120	85-170	120-240

